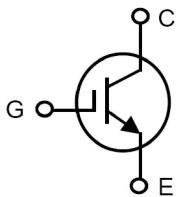


XPT™ 650V IGBTs GenX4™

IXXK160N65B4 IXXX160N65B4

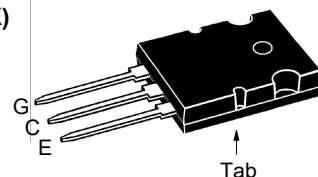
Extreme Light Punch Through
IGBT for 10-30kHz Switching



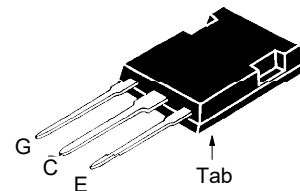
$V_{CES} = 650V$
 $I_{C110} = 160A$
 $V_{CE(sat)} \leq 1.80V$
 $t_{fi(typ)} = 90ns$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	650	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	310	A
I_{LRMS}	Leads Current Limit	160	A
I_{C110}	$T_C = 110^\circ C$	160	A
I_{CM}	$T_C = 25^\circ C$, 1ms	860	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 320$ $@V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ C$ $R_G = 10\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ C$	940	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ C$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_C	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264
(IXXK)



PLUS247
(IXXX)



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for 10-30kHz Switching
- Square RBSOA
- Short Circuit Capability
- International Standard Packages
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			25 μA 1.5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = 160A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		1.54 1.85	V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
	Min.	Typ.	Max.
g_{fs} $I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note } 1$	40	70	S
C_{ies} C_{oes} C_{res}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	8220	pF
		500	pF
		295	pF
$Q_{g(on)}$ Q_{ge} Q_{gc}	$I_C = 160\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$	425	nC
		82	nC
		193	nC
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 80\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 1\Omega$ Note 2	52	ns
		64	ns
		3.30	mJ
		220	ns
		90	ns
		1.88	3.00 mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 80\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 1\Omega$ Note 2	43	ns
		50	ns
		4.30	mJ
		220	ns
		160	ns
		2.36	mJ
R_{thJC}			0.16 $^\circ\text{C/W}$
R_{thCS}	0.15		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

Littelfuse reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or more of the following U.S. patents:	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

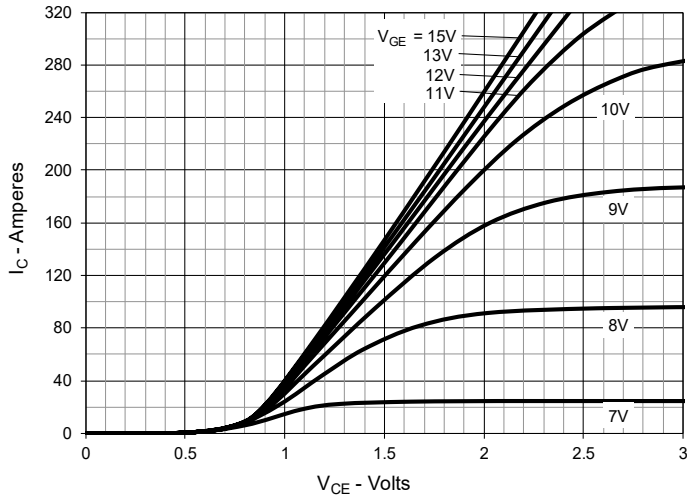


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

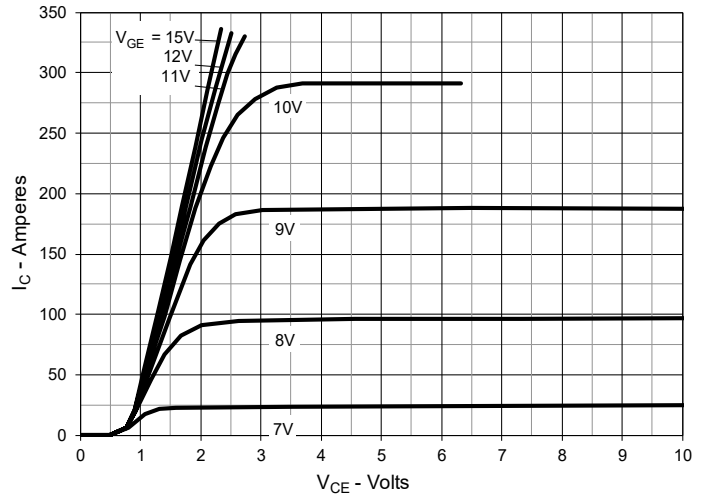


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

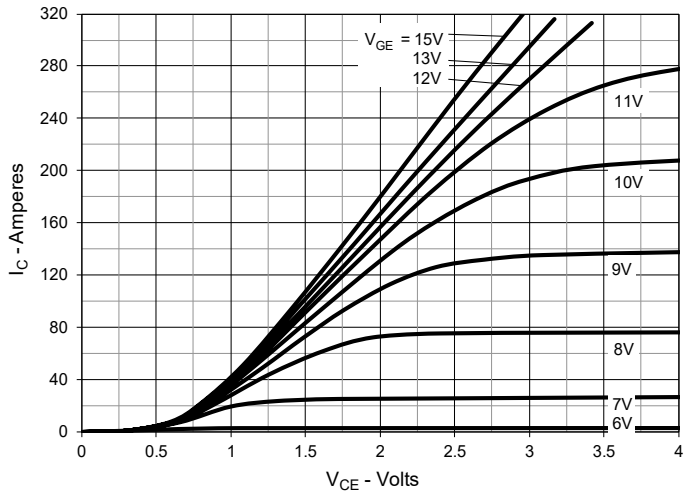


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

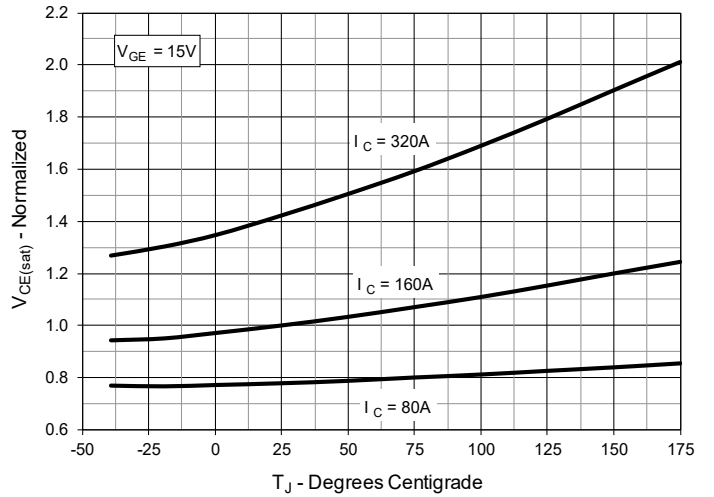


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

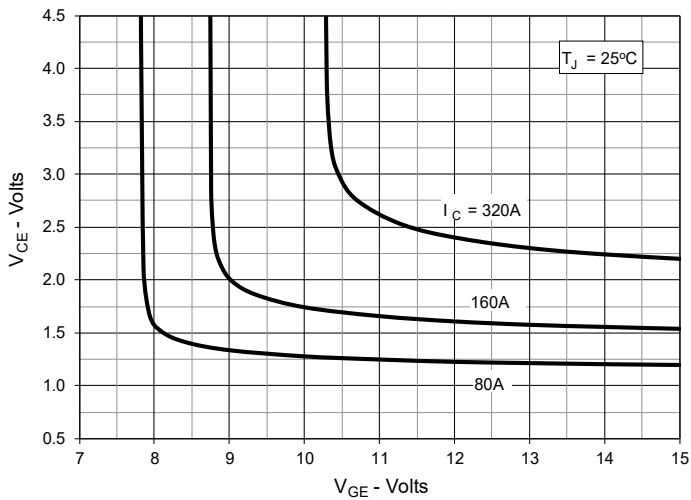


Fig. 6. Input Admittance

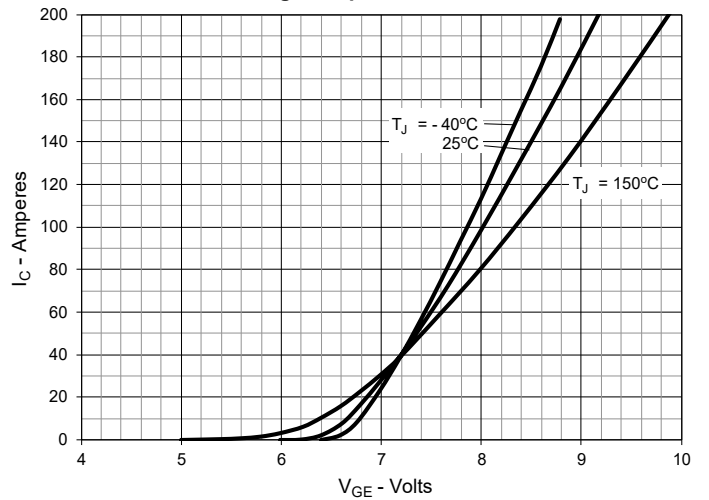


Fig. 7. Transconductance

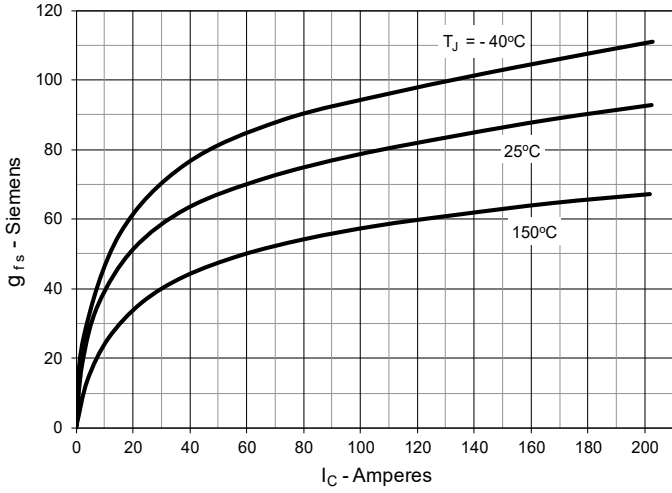


Fig. 8. Gate Charge

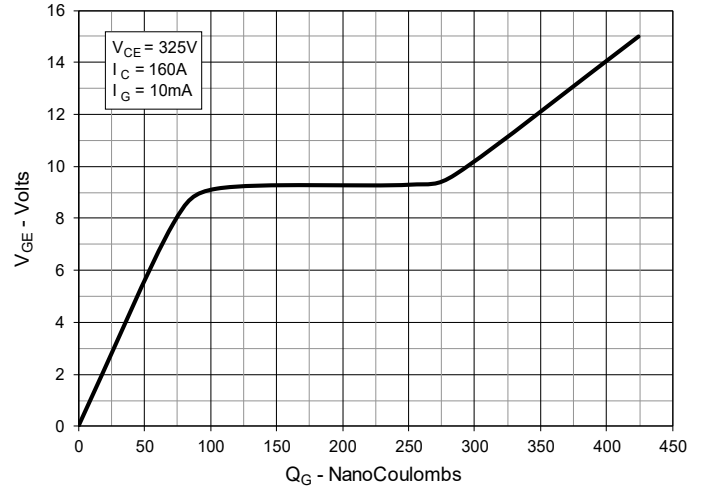


Fig. 9. Capacitance

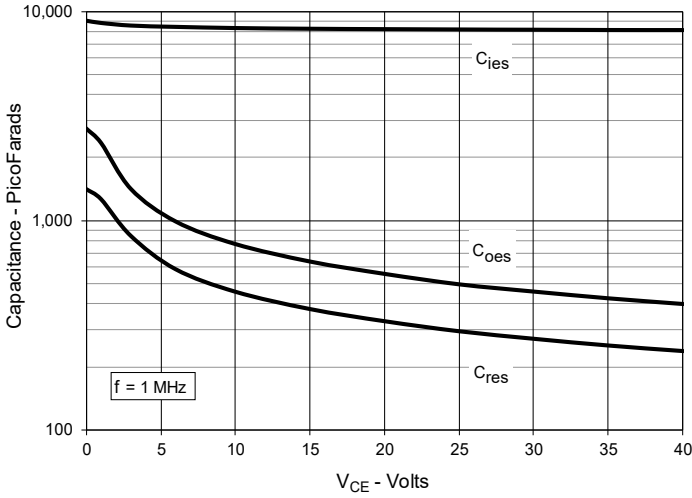


Fig. 10. Reverse-Bias Safe Operating Area

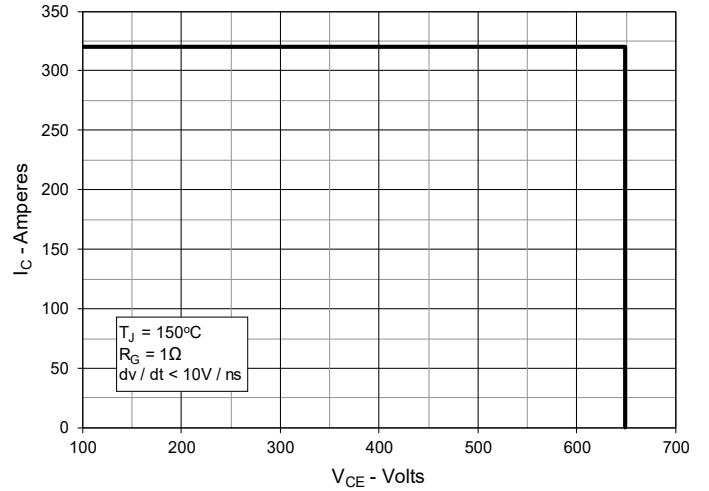


Fig. 11. Maximum Transient Thermal Impedance

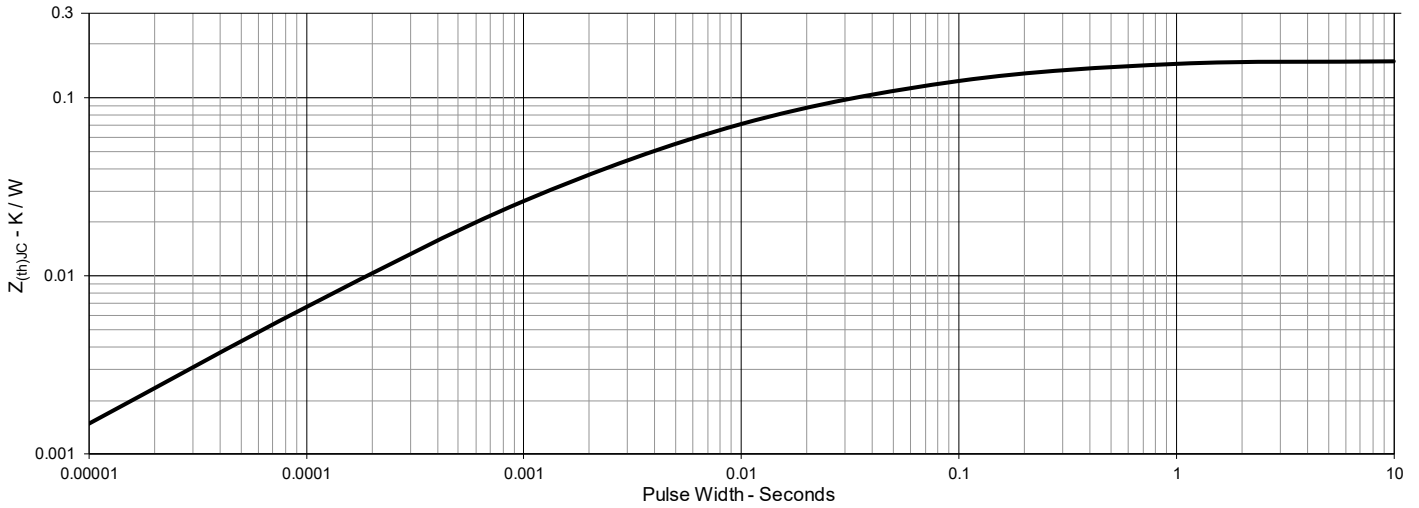


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

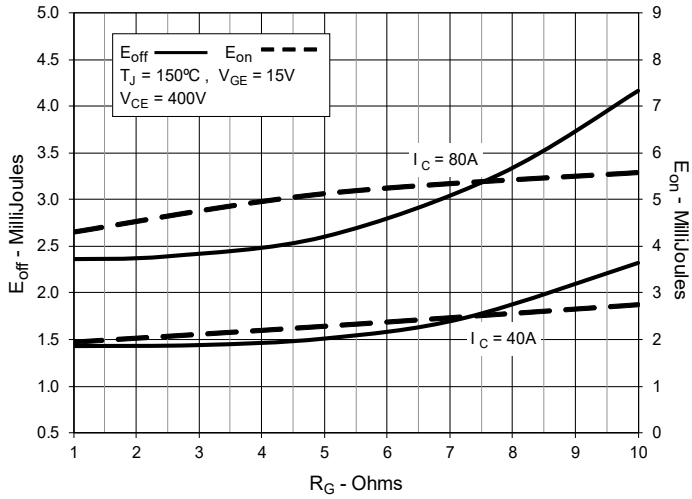


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

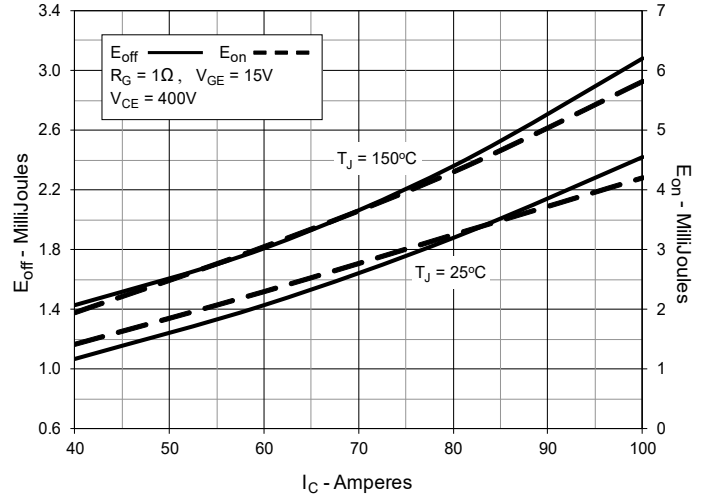


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

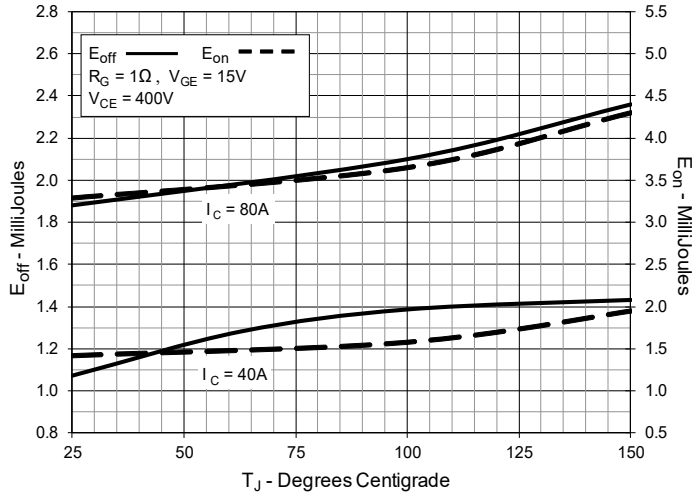


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

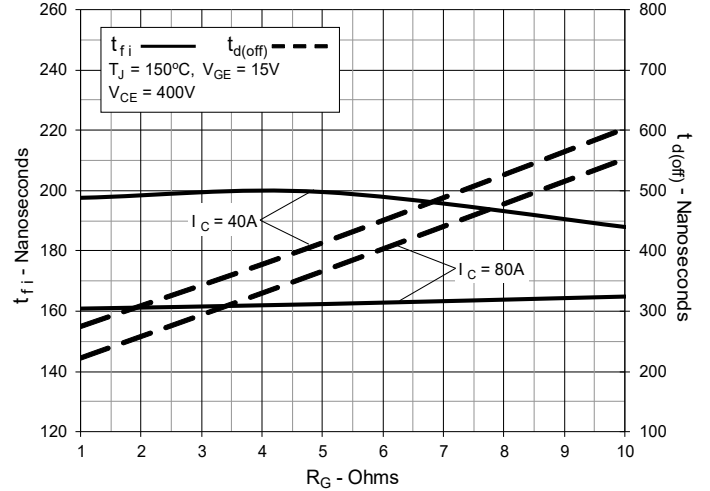


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

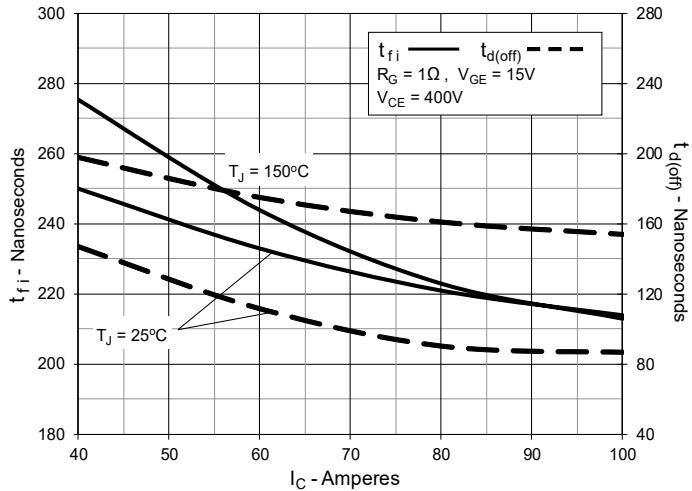


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

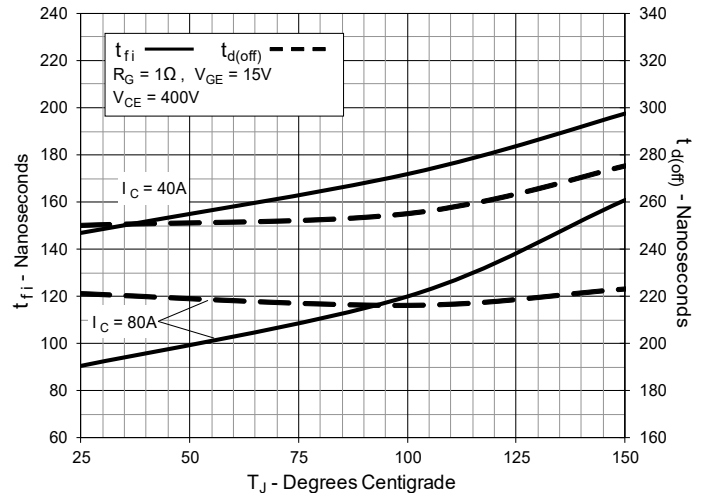


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

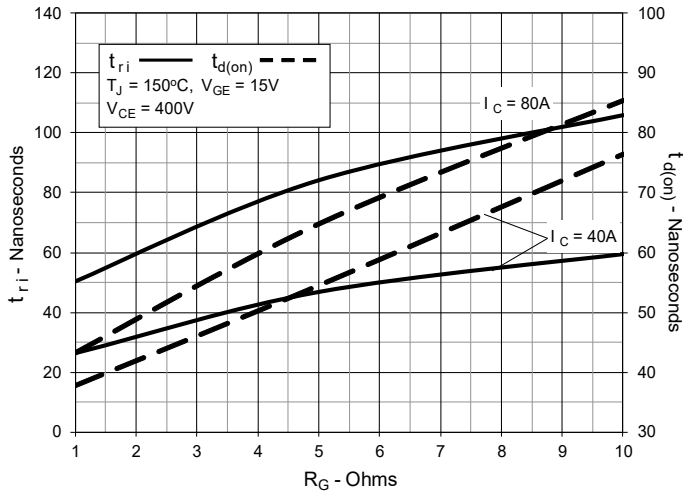


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

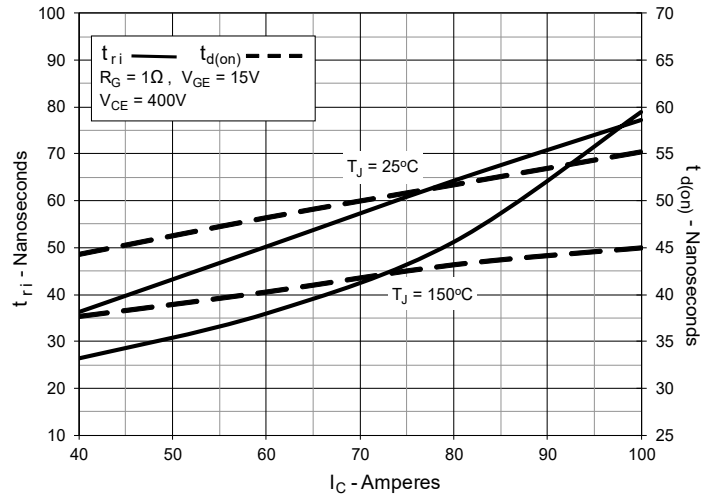
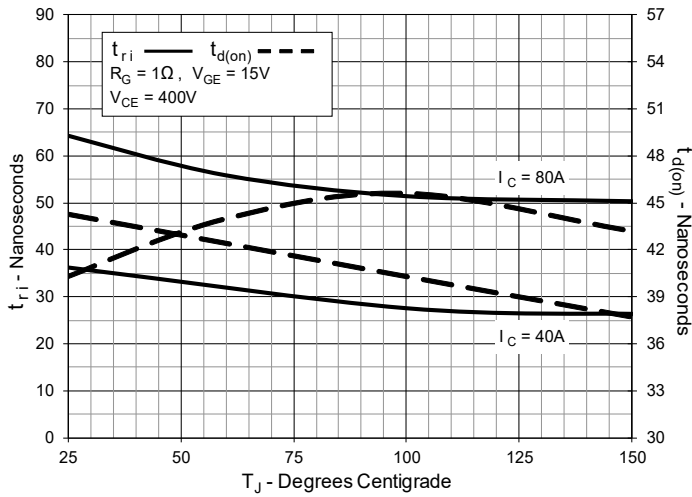
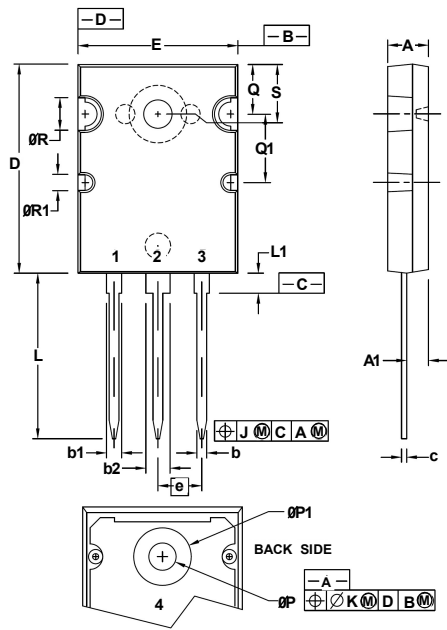


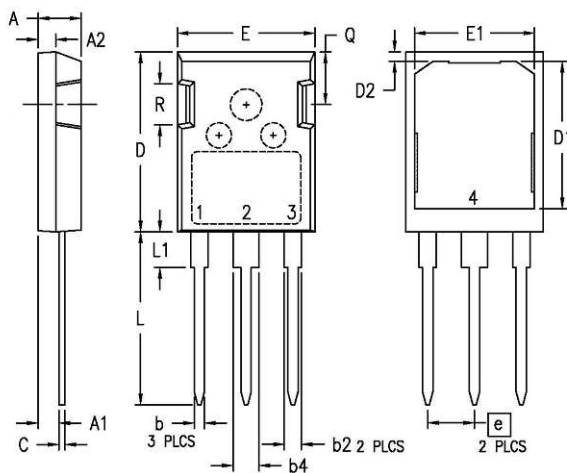
Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature



TO-264 Outline


- 1 = Gate
- 2,4 = Collector
- 3 = Emitter

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
∅P	.122	.138	3.10	3.51
∅P1	.270	.290	6.86	7.37
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
∅R	.155	.187	3.94	4.75
∅R1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS247 Outline


- 1 - Gate
- 2,4 - Collector
- 3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.520	.560	13.08	14.22
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

- NOTE: 1. This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD (R-PSIP-F3) except screw mounting hole.
 2. Pin #2 is connected to the bottom heatsink (#4).
 3. Lead finish - One of the following depending on the packaging plants.
 3.1 Matte pure tin plating on the leads and back heatsink.
 3.2 Pb free solder dip on the leads and pre Ni plated back heatsink.



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Littelfuse reserves the right to change limits, test conditions, and dimensions.
